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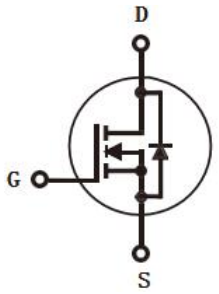
MPF7N65

Silicon N-Channel Power MOSFET

Description

The MPF7N65 uses advanced trench technology and design to provide excellent RDS(ON)with low gate charge. It can be used in a wide variety of applications.



Schematic diagram

TO-220F

General Features

① V_{DS}=7A， I_D=650V
② $R_{DS(on)(typ)}$=1.1Ω@V_{GS}=10V,I_D=3.5A
③ Low Crss:10pF@25V
④ Fast switching
⑤ Improved dv/dt capability

Application

① Switch Mode Power Supply (SMPS)
② Uninterruptible Power Supply (UPS)
③ Power Factor Correction (PFC)

Package Marking and Ordering Information

Ordering Codes	Package	Product Code	Packing
MPF7N65	TO-220F	MPF7N65	Tube

Electronic Characteristics （Tc=25℃）

Parameter	Symbol	Value		Unit
		TO-220F		
Drain-Source Voltage (V_{GS} = 0V)	V_{DSS}	650		V
Continuous Drain Current	I_D	7		A
Pulsed Drain Current (note1)	I_{DM}	28		A
Gate-Source Voltage	V_{GSS}	±30		V
Single Pulse Avalanche Energy (note2)	E_{AS}	165		mJ
Avalanche Current (note1)	I_{AS}	5.76		A
Repetitive Avalanche Energy (note1)	E_{AR}	100		mJ
Power Dissipation (T_C = 25ºC)	P_D	63	97	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150		ºC

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MPF7N65

Thermal Resistance

Parameter	Symbol	Value		Unit
		TO-220F		
Thermal Resistance, Junction-to-Case	R_{thJC}	1.98	1.29	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	60	K/W

Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 3.5A	--	1.1	1.35	Ω
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz	--	891	--	pF
Output Capacitance	C_{oss}		--	87	--	
Reverse Transfer Capacitance	C_{rss}		--	10	--	
Total Gate Charge	Q_g	V_{DD} = 520V, I_D = 7A, V_{GS} = 10V	--	32	--	nC
Gate-Source Charge	Q_{gs}		--	4.6	--	
Gate-Drain Charge	Q_{gd}		--	14	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 325V, I_D = 7A, R_G = 25 Ω	--	39	--	ns
Turn-on Rise Time	t_r		--	23	--	
Turn-off Delay Time	$t_{d(off)}$		--	137	--	
Turn-off Fall Time	t_f		--	60	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25 ºC	--	--	7.0	A
Pulsed Diode Forward Current	I_{SM}		--	--	28	
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 3.5A, V_{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t_{rr}	V_{GS} = 0V, I_S =7A, di_F/dt =100A /μs	--	575	--	ns
Reverse Recovery Charge	Q_{rr}		--	1.9	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=10mH, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25 ºC
3. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics (T_J= 25ºC)

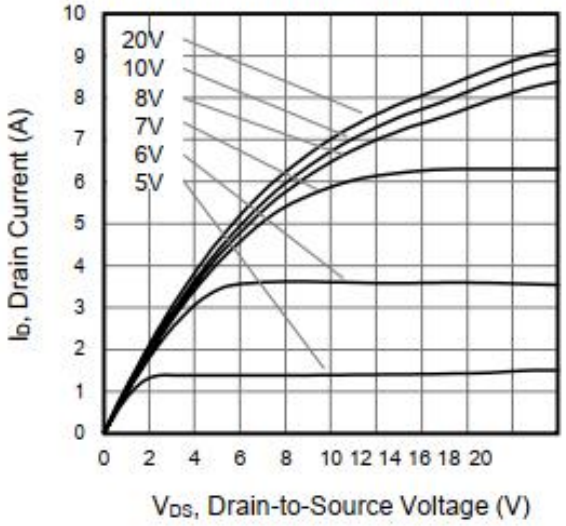


Figure 2. Body Diode ForwardVoltage

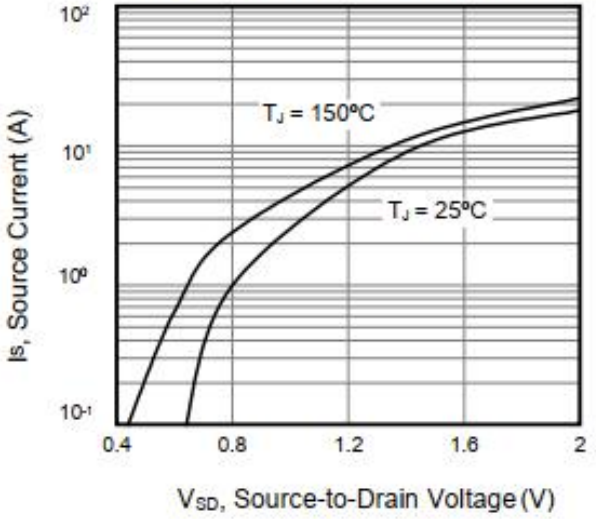


Figure 3. Drain Current vs. Temperature

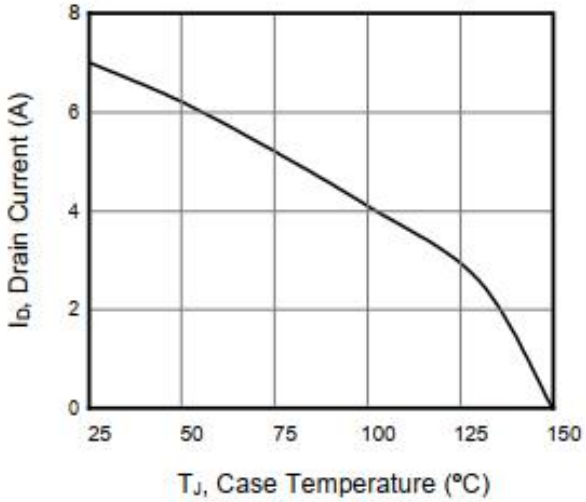


Figure 4. BV_{DSS} Variation vs.Temperature

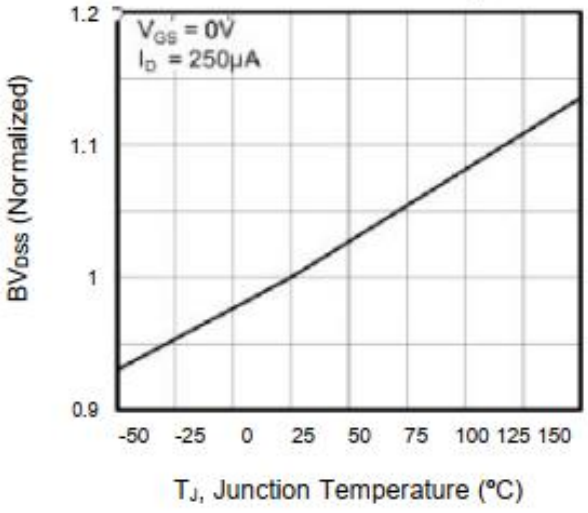


Figure 5. Transfer Characteristics

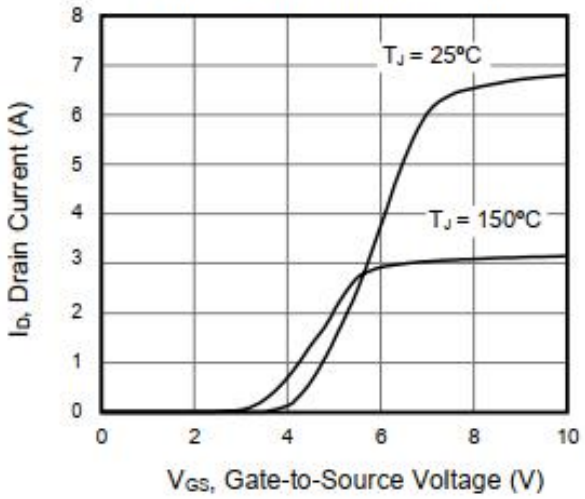
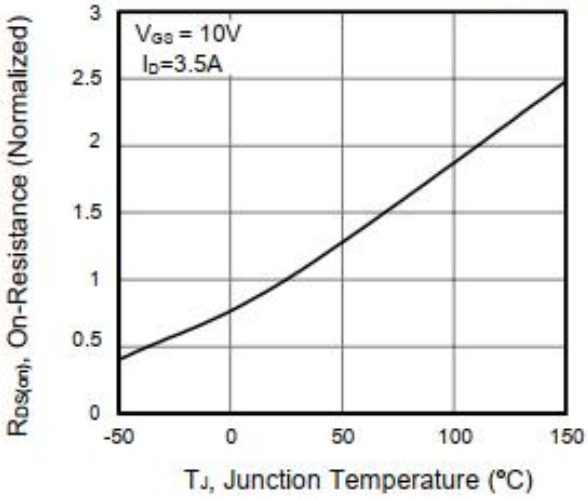


Figure 6. On-Resistance vs.Temperature



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Capacitance

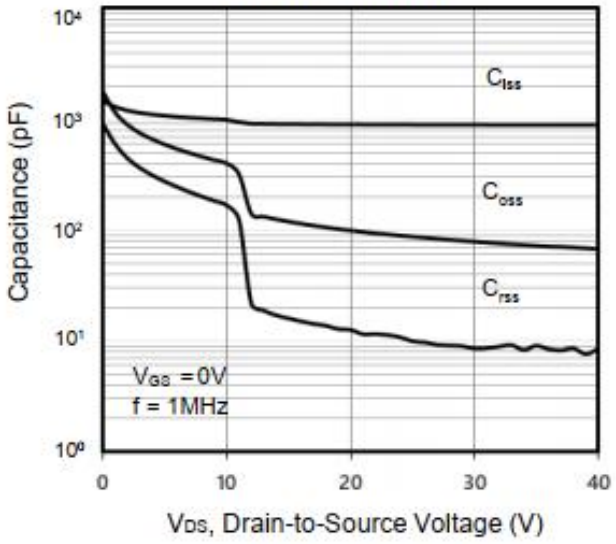


Figure 8. Gate Charge

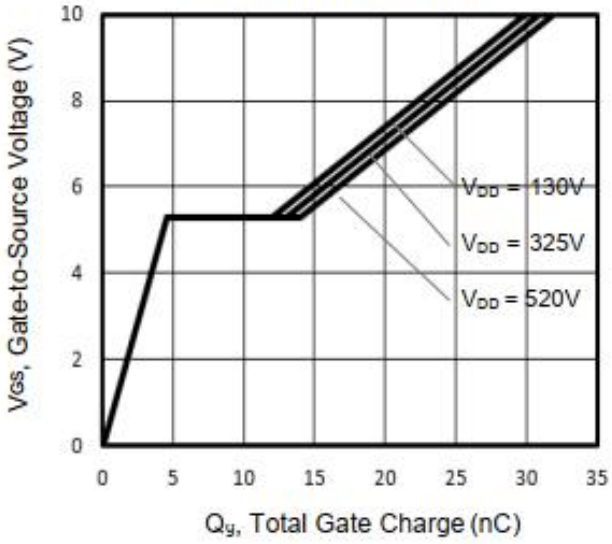


Figure 9. Transient Thermal Impedance

TO-220,TO-251,TO-252

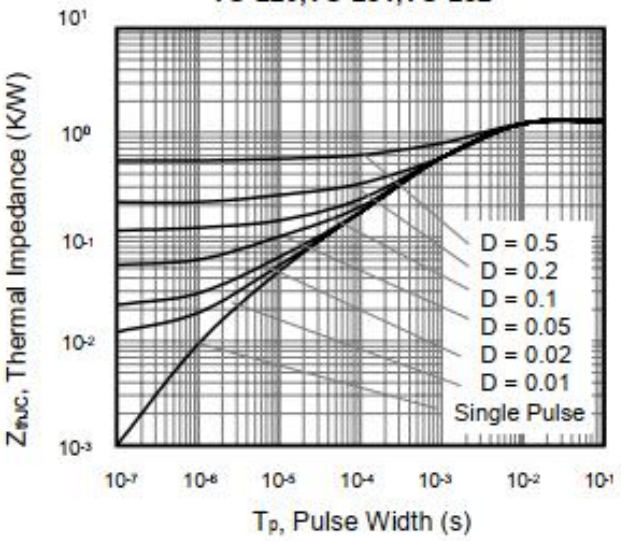


Figure 10. Transient Thermal Impedance

TO-220F

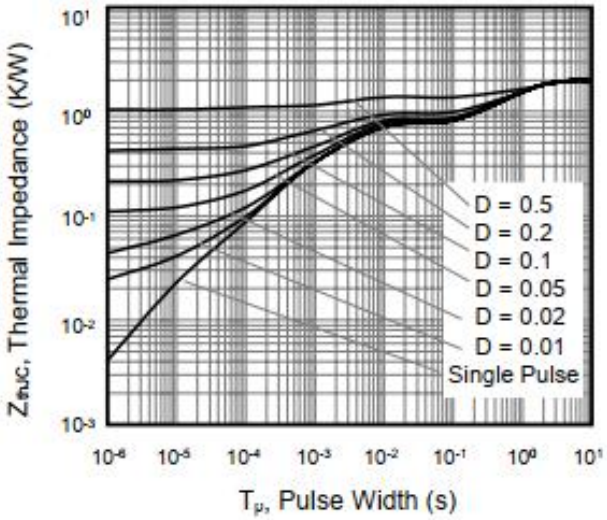


Figure A：Gate Charge Test Circuit and Waveform

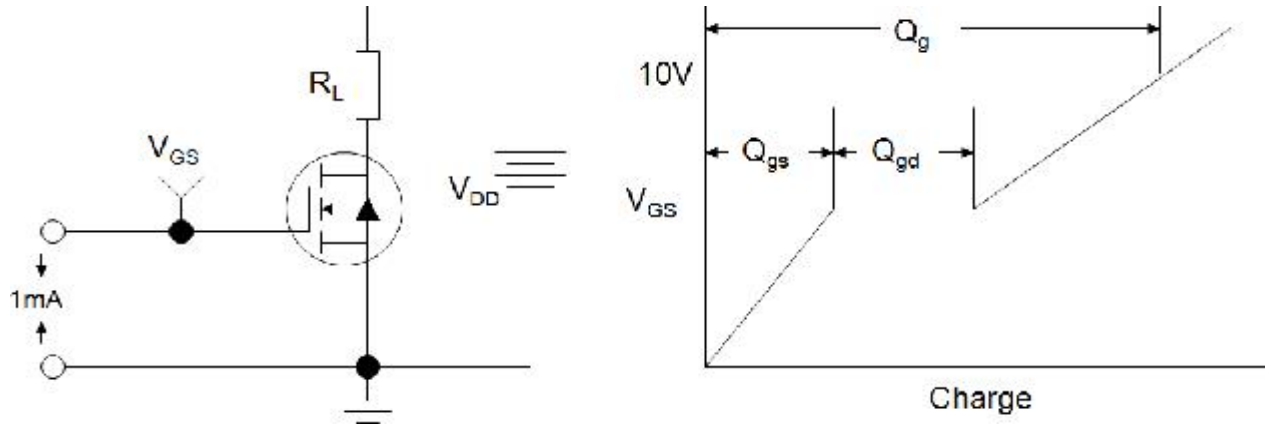


Figure B：Resistive Switching Test Circuit and Waveform

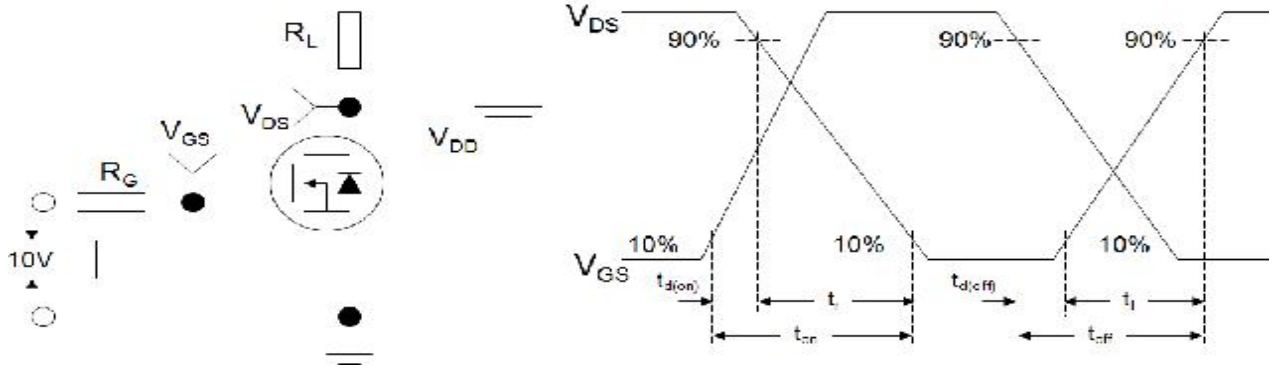
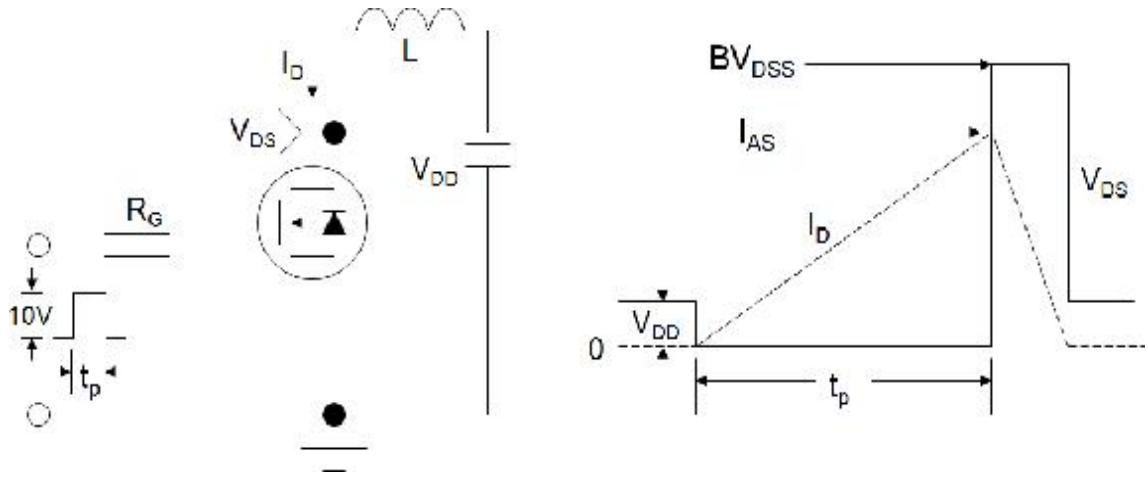
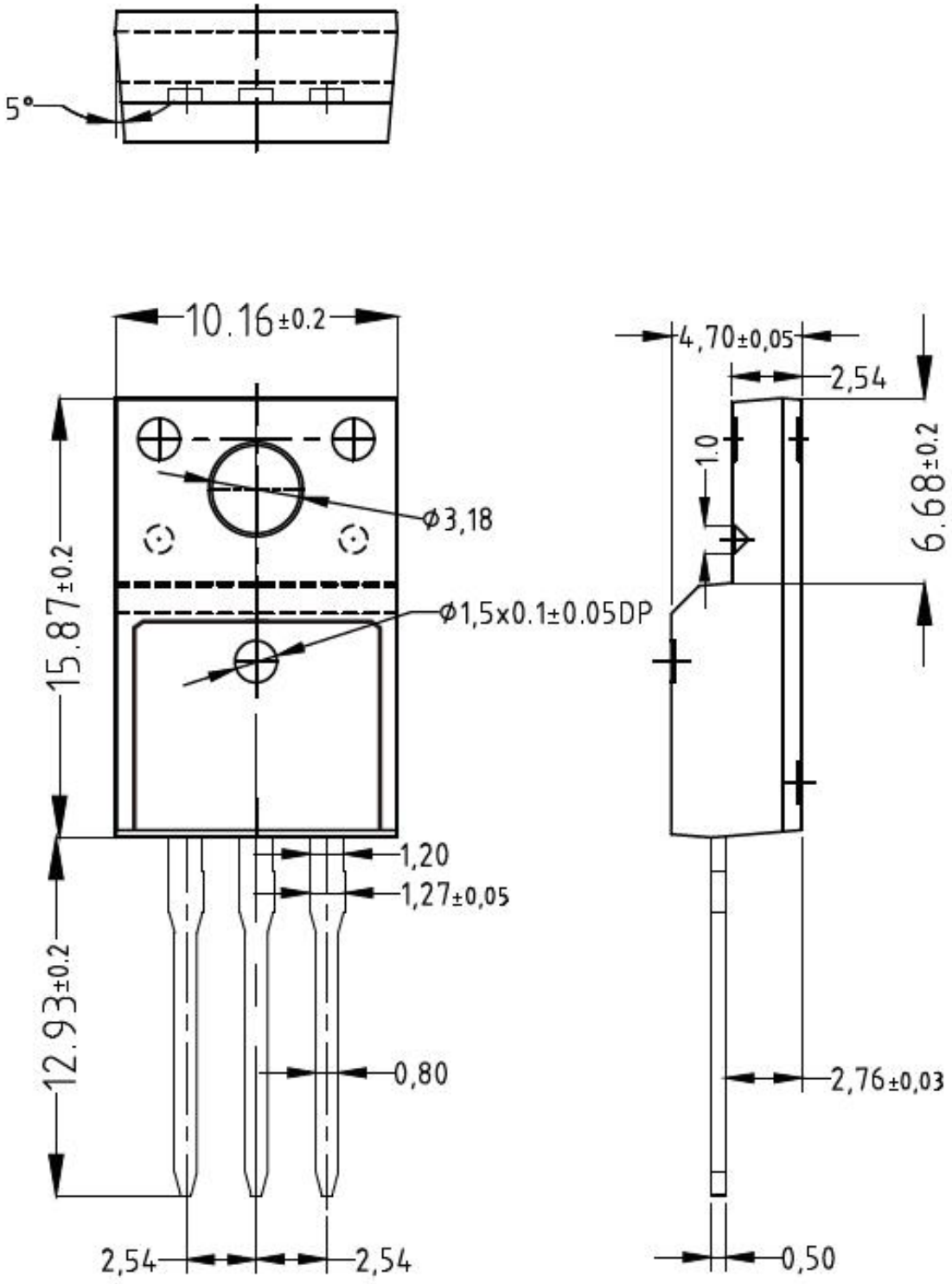


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



Package Information



NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change withoutprior notice.

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